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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-HFA90FA120</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of VS-HFA90FA120 - DIODE HEXFRED 45A 1200V SOT-227

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VS-HFA90FA120

RoHS

COMPLIANT

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 90 A



PRODUCT SUMMARY					
V_{R}	1200 V				
V _F (typical)	2.46 V				
t _{rr} (typical)	35 ns				
$I_{F(AV)}$ per module at T_C	90 A at 63 °C				
Package	SOT-227				

FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

The dual diode series configuration (VS-HFA90FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 Gen II package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode breakdown voltage	V_R		1200	V
Continuous forward current, per leg	I _F	T _C = 83 °C	45	۸
Single pulse forward current, per leg	I _{FSM}	T _J = 25 °C	400	А
Mandan and a state of the state	P _D	T _C = 83 °C	139	W
Maximum power dissipation, per leg		T _C = 100 °C	104	VV
RMS isolation voltage	V_{ISOL}	Any terminal to case, t = 1 min	2500	V
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA		1200	-	-	
		I _F = 25 A		-	2.46	3.0	V
Forward voltage	V _{FM}	I _F = 40 A	See fig. 1	-	2.68	3.3	
		I _F = 25 A, T _J = 125 °C		-	2.22	-	
		I _F = 40 A, T _J = 125 °C		-	2.52	-	
		I _F = 25 A, T _J = 150 °C		-	2.12	2.55	
		I _F = 40 A, T _J = 150 °C		-	2.43	2.96	
Reverse leakage current	I _{RM}	$V_R = V_R$ rated	See fig. 2	-	1.5	75	μA
		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{ rated}$		-	0.5	2	- mA
		T _J = 150 °C, V _R = V _R rated		-	2	5	
Junction capacitance	C _T	V _R = 1200 V	See fig. 3	-	30	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	35	-	
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 40 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	80	-	ns
		T _J = 125 °C		-	130	-	
Peak recovery current		T _J = 25 °C		-	6.8	-	A
	I _{RRM}	T _J = 125 °C		-	11.5	-	
Reverse recovery charge	0	T _J = 25 °C		-	270	-	nC
	Q _{rr}	T _J = 125 °C		-	740	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	D		-	-	0.48	
Junction to case, both legs conducting	R_{thJC}		-	-	0.24	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf.in)
Case style				SO	T-227	

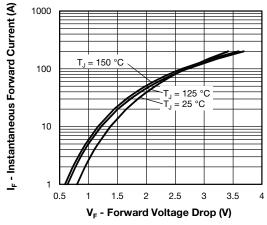


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

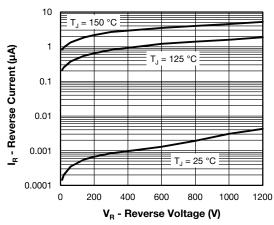


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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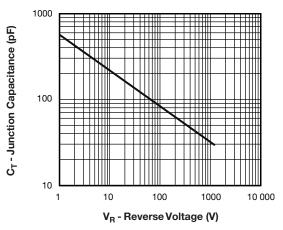


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

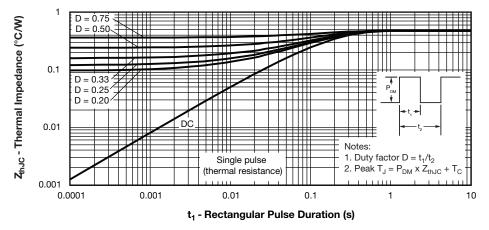


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

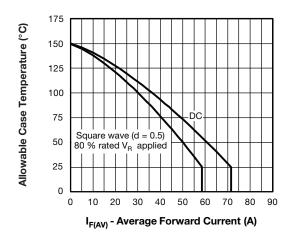
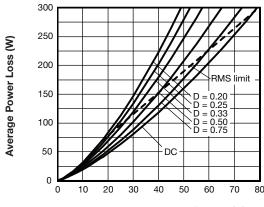


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)



I_{F(AV)} - Average Forward Current (A)

Fig. 6 - Forward Power Loss Characteristics (Per Leg)

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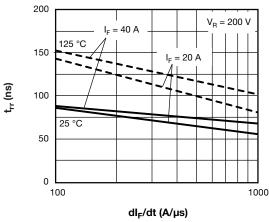
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dl_F/dt (A/μs)
Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

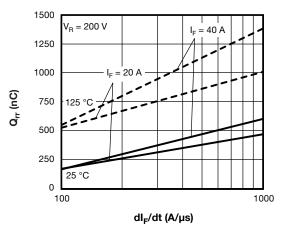


Fig. 8 - Typical Stored Charge vs. dl_F/dt

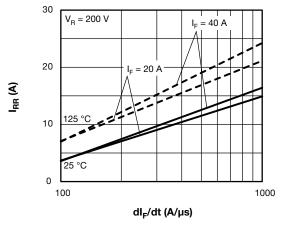


Fig. 9 - Typical Reverse Recovery Current vs. dI_{F}/dt

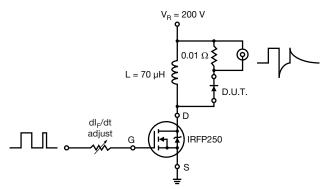


Fig. 10 - Reverse Recovery Parameter Test Circuit

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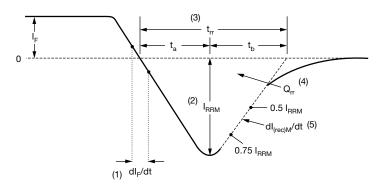
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- dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RBM}$ and 0.50 $\rm l_{RBM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

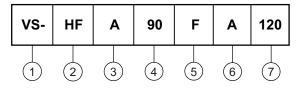
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- Process designator (A = electron irradiated)
- Average current (90 = 90 A)
- 5 Circuit configuration (2 separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (120 = 1200 V)

CIRCUIT CONFIGURATION				
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING		
2 separate diodes, parallel pin-out	F	Lead Assignment 4 0 0 3 4 1 0 0 3 3 1 1 0 0 0 1 1 1 1 1 1 1 1 1 1		

Revision: 31-May-16 5 Document Number: 94690



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